Supporting Information

**Epitaxial Growth of MgxCa1-xO on 4H-SiC (0001) and β-Ga2O3(-201) Wide Bandgap Semiconductors with ALD**

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Keywords: epitaxy, atomic layer deposition, dielectric

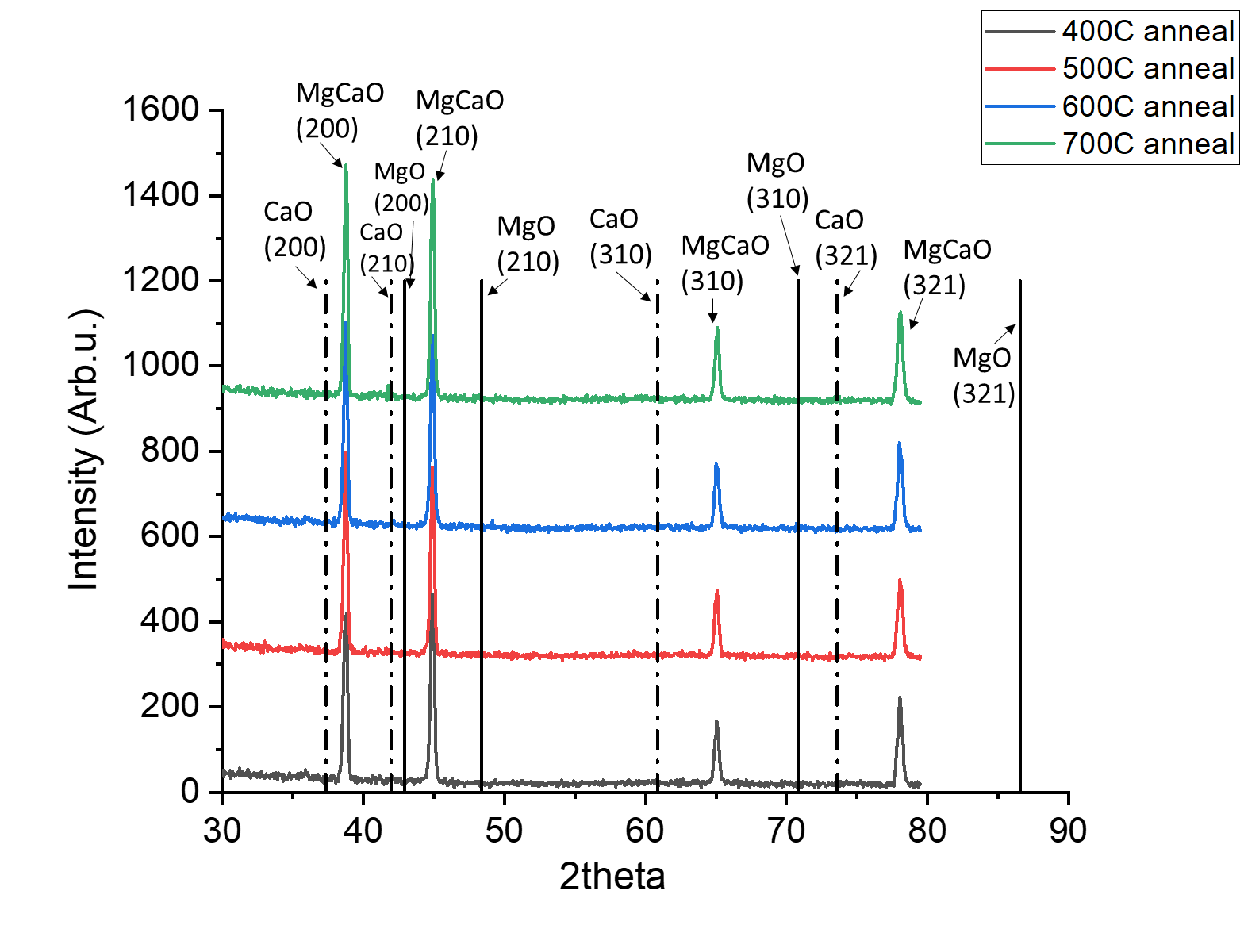


Figure S1. XRD of annealed Mg0.25Ca0.75O film under 400℃, 500℃, 600℃, 700℃. No phase separation is observed. Black dash lines are representing CaO diffraction peaks while black solid lines are MgO diffraction peaks.

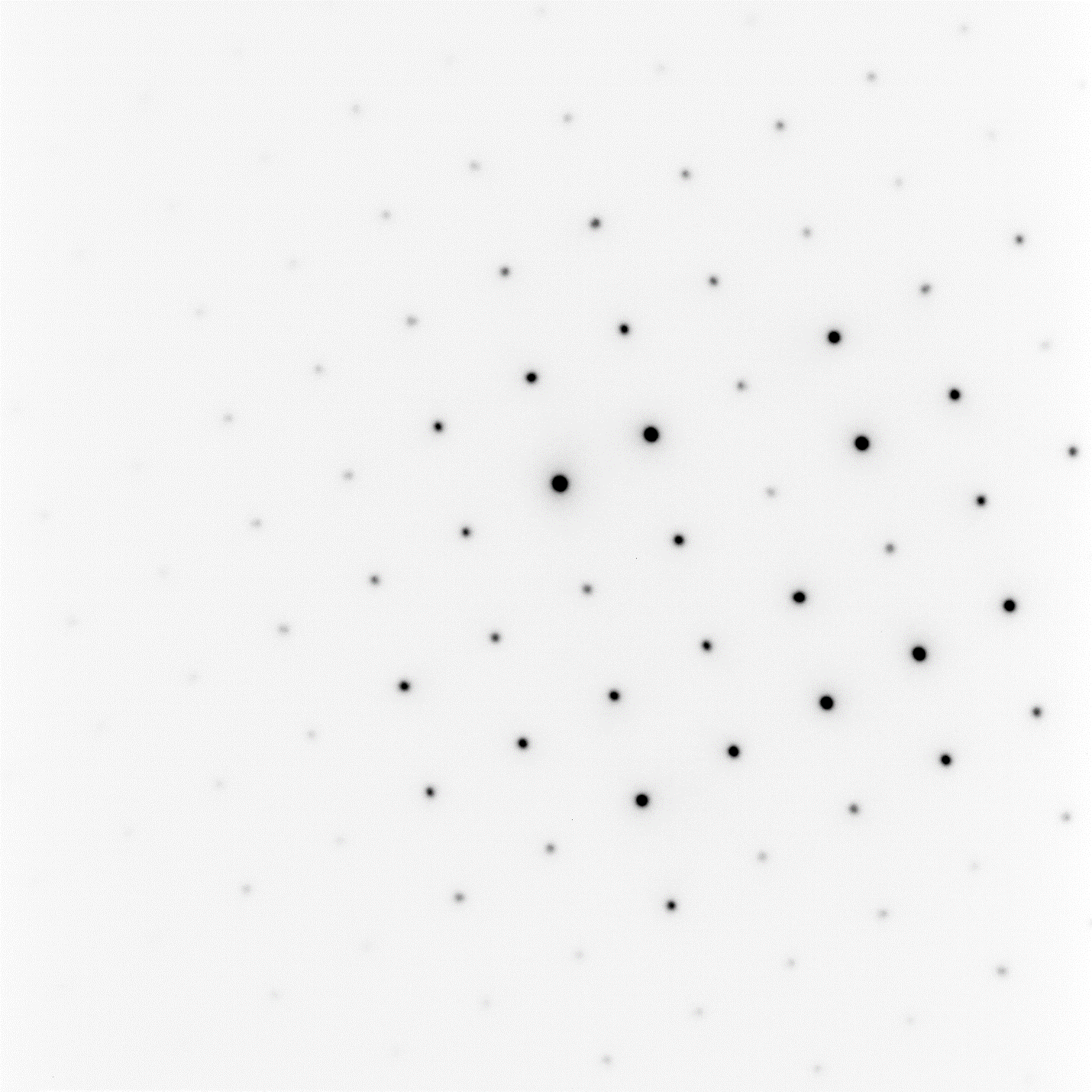


Figure S2. TEM diffraction pattern of pure Ga2O3 substrate.